

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMMC.9CP1DV1C1	APPLICATION NO. To be assigned
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Arthur Sherman	
		FILING DATE Concurrently herewith	GROUP Unknown

U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
RMS	1.	4,058,430	11/15/77	Suntola et al.	156	811	11/25/75
	2.	4,282,267	08/04/81	Köyel			
	3.	4,389,973	06/28/83	Suntola et al.	118	725	12/11/81
	4.	4,747,387	05/31/88	Posa			
	5.	4,781,269	08/02/88	Conger et al.			
	6.	4,767,494	08/30/88	Kobayashi	156	606	09/19/86
	7.	4,845,049	07/04/89	Sunakawa	437	81	03/28/88
	8.	4,851,095	07/89	Scobey et al.			
	9.	4,859,627	08/22/89	Sunakawa	437	81	07/01/88
	10.	4,876,218	10/24/89	Pessa et al.	437	107	09/26/88
	11.	4,935,661	08/90	Heinecke et al.			
	12.	4,935,661-A	06/1990	Heinecke et al.			
	13.	4,993,357	02/19/91	Scholz	118	715	12/21/89
	14.	5,080,595	10/29/91	Ziv et al.	118	722	
	15.	5,071,670	12/10/91	Kelly	427	38	
	16.	5,130,269	07/14/92	Kitahara et al.	437	111	04/25/89
	17.	5,166,092	11/24/92	Mochizuki et al.	437	105	10/30/90
	18.	5,225,366	07/08/93	Yoder	437	108	07/22/90
	19.	5,256,244	10/26/93	Ackerman	156	613	02/10/92
	20.	5,270,247	12/14/93	Sakuma et al.	437	133	07/08/92
	21.	5,278,435	01/11/94	Van Hove			
	22.	5,281,274	01/25/94	Yoder			
	23.	5,291,066	03/01/94	Neugebauer			
	24.	5,294,286	03/15/94	Neugebauer			
	25.	5,300,186	04/05/94	Kitahara			
	26.	5,308,666	04/26/94	Izumi	437	182	07/21/93
	27.	5,321,713	08/14/94	Khan			

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U.S. PATENT DOCUMENTS							
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KMS	28.	5,330,810	07/19/94	Eres			
	29.	5,356,873	10/94	Schmitt et al.			
	30.	5,374,570	12/20/94	Nasu			
	31.	5,395,791	03/07/95	Cheng			
	32.	5,443,033	08/22/95	Nishizawa			
	33.	5,443,847	08/22/95	Aucoin et al.			
	34.	5,458,084	10/17/95	Thome			
	35.	5,469,808	11/28/95	Mochizuki			
	36.	5,483,918	01/16/96	Kitahara			
	37.	5,484,884	01/16/96	Yokoyama			
	38.	5,488,582	03/05/96	Mizutani			
	39.	5,618,395	04/08/97	Gartner			
	40.	5,641,984	08/24/97	Aftergut			
	41.	5,693,139	12/02/97	Nishizawa et al.	117	89	06/15/93
	42.	5,707,880	01/13/98	Aftergut			
	43.	5,711,811	01/27/98	Suntola			
	44.	5,730,802	03/24/98	Ishizumi			
	45.	5,769,950	06/23/98	Takasu et al.			
	46.	5,855,680	01/05/99	Solinen			
	47.	5,916,365	06/99	Sherman			
	48.	5,916,365	06/1999	Sherman			
	49.	6,200,893	03/13/01	Sneh			
	50.	6,203,813	03/20/01	Gates et al.	117	104	10/19/99
	51.	6,270,572	08/07/01	Kim et al.	117	93	08/09/99
	52.	6,342,277	01/2002	Sherman			
↓	53.	US 2001/0028922	10/2001	Sandhu, Gurtej S.	427	255.27	

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FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO
KMS	54.	WO 00/83957	28.10.00	PCT	H01L21	205		
↓	55.	0 442 490 A1	21.08.91	Europe				
	56.	0 526 779 A1	10.02.93	Europe				
	57.	1 167 567 A1	02.01.02	Europe				

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
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	59.	Abeles et al., "Amorphous Semiconductor Superlattices," <u>Physical Review Letters</u> , Vol. 51, No. 21, pp. 2003-2006, (1983).
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KMS	135. Leskela, M. et al., <u>J. Less Common Metals</u> , Vol. 153, p. 219, (1989).
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FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. ASMMC.8CP1DV1C1	APPLICATION NO. To be assigned
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Arthur Sherman	
		FILING DATE Concurrently herewith	GROUP Unknown

EXAMINE R INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)
KMS	163. Ohtsuka, N. et al., "A New GaAs on Si Structure using AlAs Buffer Layers Grown by Atomic Layer Epitaxy," <u>J. Cryst. Growth</u> , Vol. 99, p.346, (1990).
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	236. Opening Claim Construction Brief of the ASM Parties Regarding the '365 Patent, Case No. C 01 2190 EDL, filed May 3, 2002.
	237. Opening Claim Construction Brief of ASM Regarding the '590 Patent, Case No. C 01 2190 EDL, filed May 3, 2002.
	238. Genus' Claim Construction Brief Regarding U.S. Patent No. 6,015,590, Case No. C 01-02190 EDL, filed May 17, 2002.
	239. Genus' Claim Construction Brief Regarding U.S. Patent No. 5,916,365, Case No. C 01-02190 EDL, filed on May 17, 2002.
	240. ASM's Claim Construction Reply Brief Regarding the '365 Patent, Case No. C 01 2190 EDL, filed on May 24, 2002.
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	242. Mahajan, A. et al. "Si atomic layer epitaxy based on Si ₂ H ₆ and remote He plasma bombardment," <u>Thin Solid Films</u> , Vol. 225, pp. 177-182 (1993).
✓	243. Sakawa, H. et al., "Digital Chemical Vapor Deposition of SiO ₂ Using a Repetitive Reaction of triethylsilane/Hydrogen and Oxidation," <u>Japanese Journal of Applied Physics</u> , Vol. 30, No. 1B, pp. L124-L127 (1990).

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INFORMATION DISCLOSURE

STATEMENT BY APPLICANT

(Multiple sheets used when necessary)

APR 27 2005

SHEET 1 OF 1

Application No.	10/683,727
Filing Date	October 10, 2003
First Named Inventor	Sherman
Art Unit	1762
Examiner	Eric B. Fuller
Attorney Docket No.	ASMMC.9CP1DV1C1

U.S. PATENT DOCUMENTS

Examiner Initials	Cite No.	Document Number Number - Kind Code (if known) Example: 1,234,567 B1	Publication Date MM-DD-YYYY	Name of Patentee or Applicant	Pages, Columns, Lines Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS

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NON PATENT LITERATURE DOCUMENTS

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KMS		ASM AMERICA, INC., and ARTHUR SHERMAN, and ASM INTERNATIONAL, N.V. v. GENUS, INC., 401 F.3d 1340, 74 U.S.P.Q.2d 1211, Fed.Cir.(Cal.), March 16, 2005.	

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